



DSS5220TQ

### 20V PNP LOW SATURATION TRANSISTOR IN SOT23

## **Description**

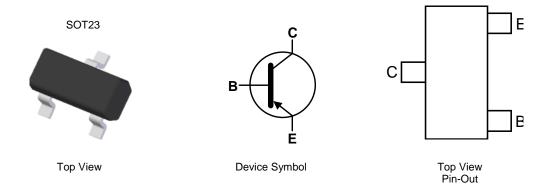
This Bipolar Junction Transistor (BJT) is designed to meet the stringent requirements of Automotive Applications.

### **Features**

- BV<sub>CEO</sub> > -20V
- I<sub>C</sub> = -2A Continuous Collector Current
- I<sub>CM</sub> = -3A Peak Pulse Current
- Low Saturation Voltage V<sub>CE(SAT)</sub> < -150mV @ -1A</li>
- R<sub>CE(SAT)</sub> = 113mΩ for a Low Equivalent On-Resistance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound; UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight 0.008 grams (Approximate)



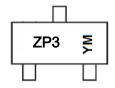
## Ordering Information (Notes 4 & 5)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
DSS5220TQ-7	Automotive	ZP3	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product\_compliance\_definitions.html.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**



ZP3 = Product Type Marking Code (See Table Above) YM = Date Code Marking

Y = Year (ex: C = 2015) M = Month (ex: 9 = September)

Date Code Key

Year	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026
Code	С	D	Е	F	G	Н		J	K	L	М	N
F												
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec



## Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	-20	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-20	V
Emitter-Base Voltage	V <sub>EBO</sub>	-7	V
Peak Pulse Collector Current	I <sub>CM</sub>	-3	А
Continuous Collector Current	Ic	-2	А

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 6)	D	600	mW	
Power Dissipation	(Note 7)	P <sub>D</sub>	1.2	W	
Thermal Desigtance, Junction to Ambient Air	(Note 6)	D	209		
Thermal Resistance, Junction to Ambient Air	(Note 7)	$R_{ heta JA}$	104	°C/W	
Thermal Resistance, Junction to Leads	(Note 8)	$R_{ heta JL}$	75		
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

## ESD Ratings (Note 9)

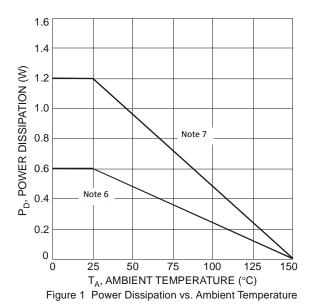
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	٧	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

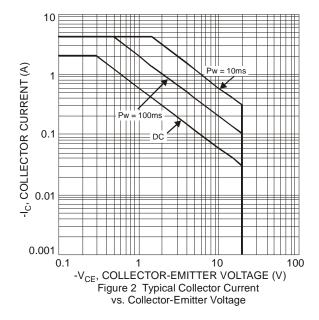
Notes:

- 6. For a device mounted on minimum recommended pad layout with 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- Same as note 6, except mounted on 25mm x 25mm 1oz copper.
  Thermal resistance from junction to solder-point (at the end of collector lead).
- 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



## **Thermal Characteristics and Derating information**





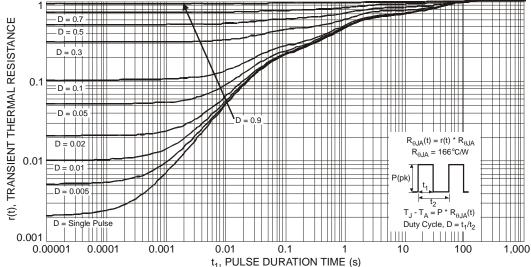


Figure 3 Transient Thermal Response



# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

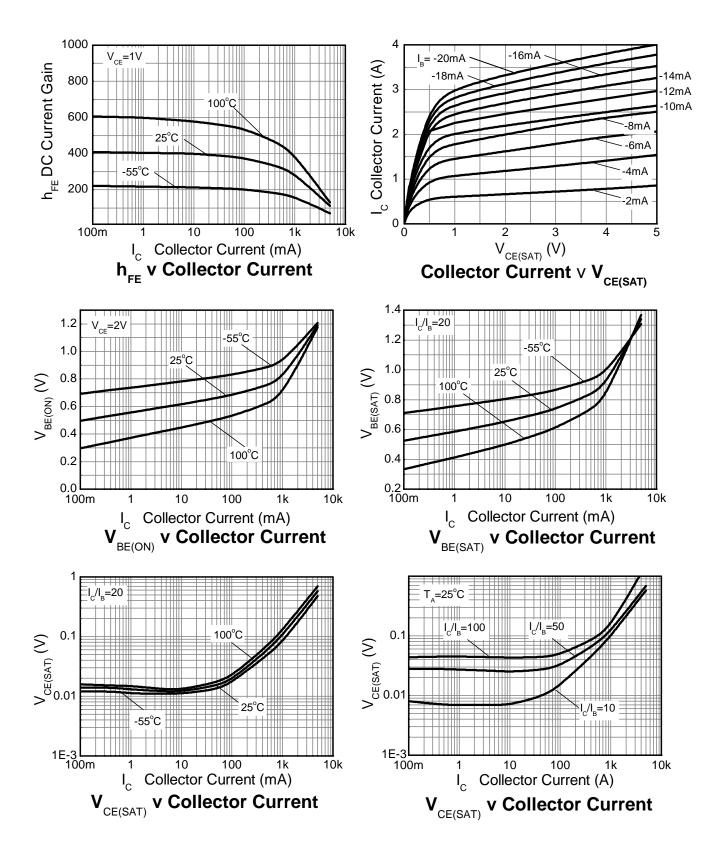
Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS	•		•			
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-20	_	_	V	I <sub>C</sub> = -100μA
Collector-Emitter Breakdown Voltage (Note 10)	BV <sub>CEO</sub>	-20	_	_	V	I <sub>C</sub> = -10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-7	_	_	V	I <sub>E</sub> = -100μA
Collector Book Cutoff Course				-100	nA	V <sub>CB</sub> = -20V, I <sub>E</sub> = 0
Collector-Base Cutoff Current	I <sub>CBO</sub>	_	_	-50	μΑ	$V_{CB} = -20V, I_E = 0, T_J = +150$ °C
Emitter-Base Cutoff Current	I <sub>EBO</sub>	_	_	-100	nA	$V_{EB} = -6V, I_{C} = 0$
ON CHARACTERISTICS (Note 10)	•		•			
		225	_	_		V <sub>CE</sub> = -2V, I <sub>C</sub> = -100mA
DC Current Gain	h	225	_	_		$V_{CE} = -2V, I_{C} = -500mA$
DC Current Gain	h <sub>FE</sub>	200	_	_		$V_{CE} = -2V, I_{C} = -1A$
		150	_	_		$V_{CE} = -2V, I_{C} = -2A$
		_	_	-80		I <sub>C</sub> = -500mA, I <sub>B</sub> = -50mA
Collector-Emitter Saturation Voltage	V	_	_	-150	mV	$I_C = -1A$ , $I_B = -50mA$
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	_	_	-250	IIIV	$I_C = -2A$ , $I_B = -100mA$
		_	_	-225		$I_C = -2A$ , $I_B = -200mA$
Equivalent On-Resistance	R <sub>CE(SAT)</sub>	_	_	113	mΩ	$I_C = -2A$ , $I_B = -200mA$
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	_	_	-1.1	V	$I_C = -2A$ , $I_B = -100mA$
Base-Emitter Turn-on Voltage	V <sub>BE(ON)</sub>	_	_	-1.2	V	V <sub>CE</sub> = -2V, I <sub>C</sub> = -1A
SMALL SIGNAL CHARACTERISTICS			•	•	•	•
Transition Frequency	f <sub>t</sub>	100	_	_	MHz	V <sub>CE</sub> = -5V, I <sub>C</sub> = -100mA, f = 100MHz
Collector-Base Capacitance	C <sub>cbo</sub>	_	_	50	pF	V <sub>CB</sub> = -10V, f = 1MHz

Note:

10. Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.



## Typical Electrical Characteristics ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

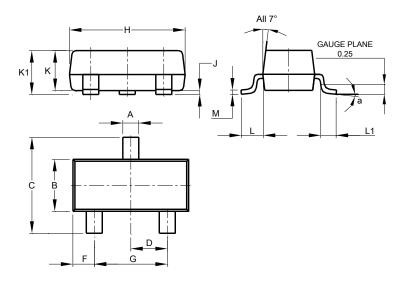




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT23

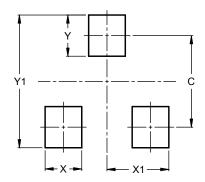


	SOT23						
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°					
All	Dimens	ions in	mm				

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9

June 2017

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